

# Specification Sheet

**Boron Doped P Type Silicon Wafer****(4 inches, Single Side Polished)****Stock No: NS6130-10-1110, CAS: 7440-21-3**

<b>Product</b>	:	<b>Silicon Wafer 4"</b>
Stock No	:	NS6130-10-1110
CAS	:	7440-21-3
Diameter	:	4"
Thickness	:	300±10µm
Dopant	:	Boron
Crystal Orientation	:	< 100>
Type	:	P
Growth Method	:	CZ/FZ
Resistivity	:	1.0-5.0Ω.cm
TTV	:	< 10.0µm
STIR	:	< 2µm
GLOBAL TIR	:	< 5µm
Warp	:	< 50.0µm
LPD	:	< 30 counts @ particles size>0.3µm
Laser Mark	:	None
Edge Profile	:	Rounded
Front Surface	:	Polished
Back Surface	:	Polished
Bow	:	< 50.0µm
<b>Main Inspect Verifier</b>	:	<b>Manager QC</b>

**Note:** Product Specification are subject to amendment and may change over time

## Characterization of Boron Doped P Type Silicon Wafer



Boron Doped P Type Silicon Wafer



**NANOSHEL**  
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